

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

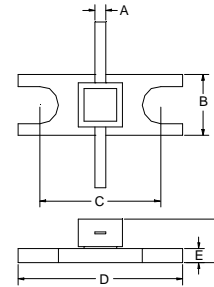
The **ASI OSC-0.3C** is Designed for

**FEATURES:**

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- **Omnigold™** Metalization System

**MAXIMUM RATINGS**

<b>I<sub>C</sub></b>	225 mA
<b>V<sub>CB</sub></b>	25 V
<b>P<sub>DISS</sub></b>	5.0 W @ T <sub>C</sub> = 25 °C
<b>T<sub>J</sub></b>	-65 °C to +200 °C
<b>T<sub>STG</sub></b>	-65 °C to +200 °C
<b>θ<sub>JC</sub></b>	30 °C/W

**PACKAGE STYLE .138 2L FLG**


DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.025 / 0.635	
B	.138 / 3.505	
C	.275 / 6.985	
D	.375 / 9.525	
E	.031 / 0.787	
F	.062 / 1.575	

**ORDER CODE: ASI10636**
**CHARACTERISTICS** T<sub>C</sub> = 25 °C

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
<b>BV<sub>CEO</sub></b>	I <sub>C</sub> = 1.0 mA			16			<b>V</b>
<b>BV<sub>CBO</sub></b>	I <sub>C</sub> = 100 μA			25			<b>V</b>
<b>I<sub>EBO</sub></b>	I <sub>EB</sub> = 1.0 V					2.0	<b>μA</b>
<b>I<sub>CBO</sub></b>	V <sub>CB</sub> = 15 V					500	<b>μA</b>
<b>h<sub>FE</sub></b>	V <sub>CE</sub> = 8.0 V	I <sub>C</sub> = 100 mA		20		200	<b>---</b>
<b>C<sub>OB</sub></b>	V <sub>CB</sub> = 10 V	f = 1.0 MHz				1.5	<b>pF</b>
<b>η<sub>C</sub></b>	V <sub>CC</sub> = 12 V	P <sub>OUT</sub> = 0.3 W	f = 7.5 GHz		22		<b>%</b>
<b> S<sub>21C</sub> <sup>2</sup></b>	V <sub>CE</sub> = 8.0 V	I <sub>C</sub> = 100 mA	f = 1.0 GHz	4.0			<b>dB</b>
<b>P<sub>OSC</sub></b>	V <sub>CC</sub> = 12 V	I <sub>C</sub> = 120 mA	f = 7.5 GHz		320		<b>mW</b>